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9.63% efficient flexible Cu₂ZnSn(S,Se)₄ solar cells via scalable doctor-blading in ambient condition

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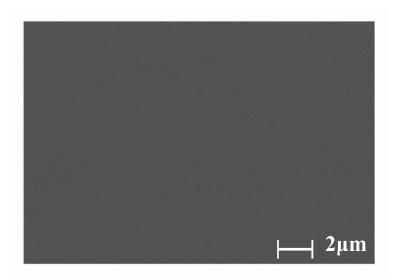


Figure S1. The top-view SEM micrograph of the Na-0 CZTS precursor film.

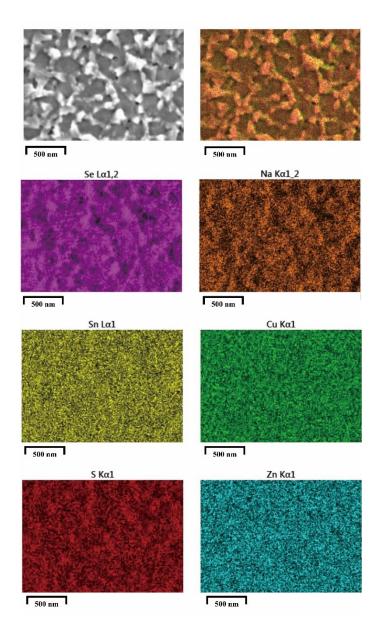


Figure S2. The EDX elemental mapping of the Na-all sample.

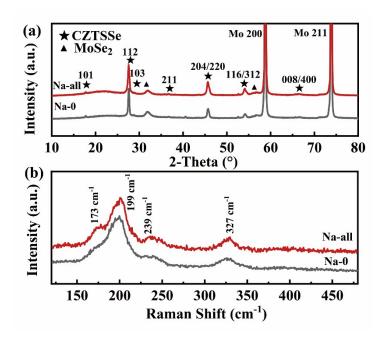


Figure S3. (a) XRD patterns and (b) Raman spectra of Na-0 and Na-all CZTSSe thin films on the Mo foil.

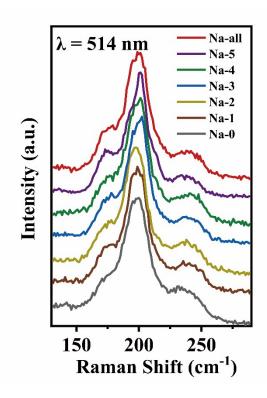


Figure S4. Raman spectra of Na-0 \sim Na-all at 130 \sim 290 cm⁻¹, measured with an excitation wavelength of 514 nm.

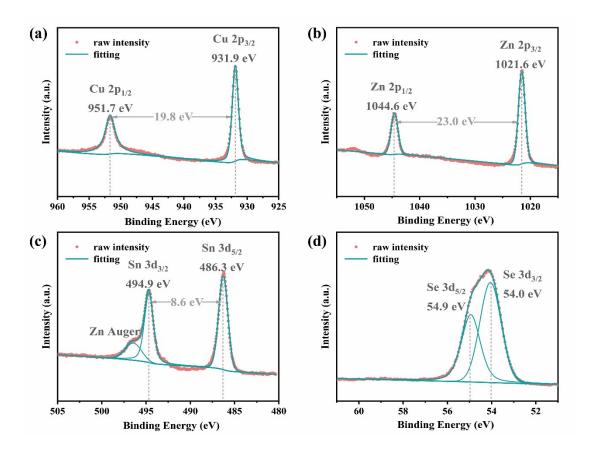


Figure S5. XPS spectra of (a) Cu 2p, (b) Zn 2p, (c) Sn 3d, and (d) Se 3d in the Na-4 CZTSSe.

Table S1. FWHM of the (112) plane and the corresponding crystallite size estimated from the Scherrer equation for Na-0 \sim Na-5 samples.

Sample	FWHM	Size (nm)
Na-0	0.310	26.12
Na-1	0.283	28.60
Na-2	0.295	27.43
Na-3	0.288	28.11
Na-4	0.242	33.44
Na-5	0.297	27.24

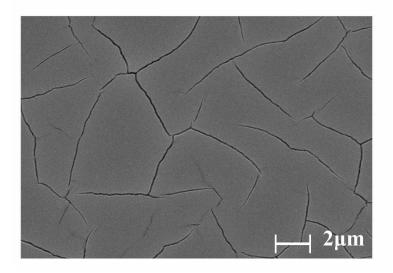


Figure S6. The top-view SEM micrograph of the Na-5 CZTS precursor film.

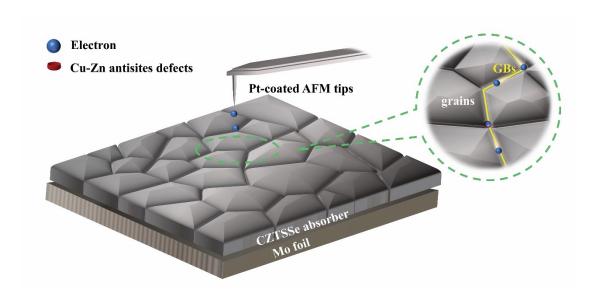


Figure S7 A schematic figure shows that the injected electrons from AFM tip transport along GBs, and the enlarged view illustrates that the Cu-Zn antisites defects at GBs reduce the mobility of electrons by trapping them, which leads to a lower current.